# 18-600 Foundations of Computer Systems

## Lecture 10: "The Memory Hierarchy"

John P. Shen & Gregory Kesden October 2, 2017

#### Required Reading Assignment:

- Chapter 6 of CS:APP (3<sup>rd</sup> edition) by Randy Bryant & Dave O'Hallaron
- Recommended Reference:
  - Sec. 1 & Sec. 3: Bruce Jacob, "The Memory System: You Can't Avoid It, You Can't Ignore It, You Can't Fake It," Synthesis Lectures on Computer Architecture 2009.



Carnegie Mellon University 1

10/02/2017 (© John Shen)

18-600 Lecture #10

# 18-600 Foundations of Computer Systems

## Lecture 10: "The Memory Hierarchy"

- A. Memory Technologies
- B. Main Memory Implementation
  - a. DRAM Organization
  - b. DRAM Operation
  - c. Memory Controller
- C. Disk Storage Technologies



10/02/2017 (© John Shen)

#### From Lec #9 ...



# Integrating Map Table with the ARF



(a)



9/27/2017 (©J.P. Shen)

18-600 Lecture #9

#### From Lec #9 ...



9/27/2017 (©J.P. Shen)

18-600 Lecture #9

From Lec #9 ...

# Reorder Buffer Implementation



**(a)** 



- Reorder Buffer
  - "Bookkeeping"
  - Can be instructiongrained, or blockgrained (4-5 ops)



18-600 Lecture #10

#### Carnegie Mellon University 7

10/02/2017 (© John Shen)



ia1

ia2

ia3

ia4

ia5

ia6

ia7

.L2:

ia8

ia9

18-600 Lecture #10



.L3:

ia1

ia2

ia3

ia4

ia5

ia6

ia7

.L2:

ia8

ia9

18-600 Lecture #10



.L3:

ia1

ia2

ia3

ia4

ia5

ia6

ia7

.L2:

ia8

ia9

18-600 Lecture #10

Carnegie Mellon University <sup>10</sup>



.L3:

ia1

ia2

ia3

ia4

ia5

ia6

ia7

.L2:

ia8

ia9

18-600 Lecture #10



18-600 Lecture #10



18-600 Lecture #10

Carnegie Mellon University <sup>13</sup>





18-600 Lecture #10





18-600 Lecture #10



18-600 Lecture #10

From Lec #9 ...

# Prefetching Data Cache



18-600 Lecture #10

Carnegie Mellon University <sup>19</sup>

#### From Lec #9 ...

## **Cortex-A9 Single Core Microarchitecture**



10/02/2017 (© John Shen)

18-600 Lecture #10



18-600 Lecture #10

#### Carnegie Mellon University <sup>21</sup>



## State-of-the-art branch prediction

- Fine tuned 0-cycle branch prediction for better IPC
  - Further optimized from Cortex-A73
  - Sustains required instruction bandwidth to the core even on tight loops
- Resources for micro-BTACs, return stack and static branch predictors unchanged
  - Sustains additional performance required by Cortex-A75



#### ©ARM 2017

ARM

### High-performance processor core



- 3-way superscalar high-performance pipeline
  - Single cycle decode with instruction fusing and micro-ops
- 7 independent high-performance issue queues
  - 2x Load/Store, 2x NEON/FPU, 1x Branch and 2x Integer core
- Increased capacity to sustain operation under LI miss / L2 hit
  - 12 entries for integer core to maximise on inflight instructions and out-of-order capabilities
  - 8 entries for Load/Store and NEON/FPU



#### ARM

### High-throughput data path

- LI D-Cache, 64KB, 4-way set associative
  - VIPT with PIPT programmer's view
  - Load Store Unit extended to 16 slots
  - Increased core ↔ L1 cache bandwidth
- Aggressive Out-of-Order support
  - Support Read-after-Write OoO with filtering



#### ARM

#### ©ARM 2017

# Typical Computer Organization



10/02/2017 (© John Shen)

18-600 Lecture #10

#### Memory Hierarchy (where do all the bits live?) **Register File** 32 words, sub-nsec L1 cache (SRAM) ~32 KB, ~nsec CPU Memory bstraction L2 cache (SRAM) 512 KB ~ 1MB, many nsec L3 cache, (SRAM) Main Memory (DRAM) 2-8 GB, ~100 nsec **Disk Storage** 200-1K GB, ~10 msec

#### Carnegie Mellon University <sup>26</sup>

# Bus Structure Connecting CPU and Memory

- A bus is a collection of parallel wires that carry address, data, and control signals.
- Buses are typically shared by multiple devices.



## Memory Read & Write Transactions



10/02/2017 (© John Shen)

18-600 Lecture #10

# "Random Access" Memories (RAM)



- Key features
  - RAM is traditionally packaged as a chip.
  - Basic storage unit is normally a cell (one bit per cell).
  - Multiple RAM chips form a memory.
- RAM comes in two varieties:
  - SRAM (Static RAM)
  - DRAM (Dynamic RAM)

## SRAM (Static Random Access Memory)



Read Sequence

- 1. address decode
- 2. drive row select
- 3. selected bit-cells drive bitlines (entire row is read together)
- 4. diff. sensing and col. select (data is ready)
- 5. precharge all bitlines (for next read or write)

Access latency dominated by steps 2 and 3 Cycling time dominated by steps 2, 3 and 5 step 2 proportional to 2<sup>n</sup>

step 3 and 5 proportional to 2<sup>m</sup>

# DRAM (Dynamic Random Access Memory)



Bits stored as charges on node capacitance (non-restorative)

- bit cell loses charge when read
- bit cell loses charge over time

#### **Read Sequence**

- 1~3 same as SRAM
- 4. a "flip-flopping" sense amp amplifies and regenerates the bitline, data bit is mux' ed out
- 5. precharge all bitlines

Refresh: A DRAM controller must periodically read all rows within the allowed refresh time (10s of ms) such that charge is restored in cells

10/02/2017 (© J.P. Shen)

## DRAM vs. SRAM

- DRAM (used in main memories)

  - Higher density (1T 1C cell)
  - Lower cost  $\leftarrow$  1x cost
  - Requires refresh and READs are destructive
  - Manufacturing requires putting capacitor and logic together
- SRAM (used in cache memories)
  - □ Faster access (no capacitor) ← 1x access time
  - Lower density (6T cell)
  - Higher cost ← 100x cost
  - No need for refresh and non-destructive READs
  - Manufacturing compatible with logic process (no capacitor)

# 18-600 Foundations of Computer Systems

# Lecture 10: "The Memory Hierarchy"

### A. Memory Technologies

### B. Main Memory Implementation

### a. DRAM Organization

#### b. DRAM Operation

#### c. Memory Controller

C. Disk Storage Technologies



10/02/2017 (© John Shen)

# **DRAM** Chip Organization



- Optimized for density, not speed
- Data stored as charge in capacitor
- Discharge on reads => destructive reads
- Charge leaks over time
  - refresh every 64ms
- Cycle time roughly twice access time
- Need to precharge bitlines before access

18-600 Lecture #10

# DRAM Chip Organization



- Address pins are time-multiplexed
  - Row address strobe (RAS)
  - Column address strobe (CAS)
- New RAS results in:
  - Bitline precharge
  - Row decode, sense
  - Row buffer write (up to 8K)
- New CAS

۰,

- Read from row buffer
- Much faster (3x)
- Streaming row accesses
  desirable

# **DRAM Bank Organization**



- Read access sequence:
  - 1. Decode row address & drive word-line
  - 2. Selected bits drive bit-lines
    - Entire row read
  - 3. Amplify row data
  - 4. Decode column address & select subset of row
    - Send to output
  - 5. Precharge bit-lines
    - For next access
# The DRAM Chip

- Consists of multiple banks (2-16 in Synchronous DRAM)
- Banks share command/address/ data buses
- The chip itself has a narrow interface
  (4-16 bits per read)





10/02/2017 (© J.P. Shen)

18-600 Lecture #10

### DRAM Rank and Module

- Rank: Multiple chips operated together to form a wide interface
- All chips comprising a rank are controlled at the same time
  - Respond to a single command
  - Share address and command buses, but provide different data
- A DRAM module consists of one or more ranks
  - E.g., DIMM (dual inline memory module)
  - This is what you plug into your motherboard
- If we have chips with 8-bit interface, to read 8 bytes in a single access, use 8 chips in a DIMM



10/02/2017 (© J.P. Shen)

18-600 Lecture #10

### A 64-bit Wide DIMM (One Rank)



- Advantages:
  - Acts like a highcapacity DRAM chip with a wide interface
  - Flexibility: memory controller does not need to deal with individual chips

#### Disadvantages:

Granularity: Accesses
 cannot be smaller than
 the interface width

10/02/2017 (© J.P. Shen)

18-600 Lecture #10



10/02/2017 (© John Shen)

18-600 Lecture #10

### Rank and Channel



10/02/2017 (© J.P. Shen)

18-600 Lecture #10

### DRAM Channels



- 2 Independent Channels: 2 Memory Controllers (Above)
- 2 Dependent/Lockstep Channels: 1 Memory Controller with wide interface (Not Shown above)

10/02/2017 (© John Shen)

18-600 Lecture #10

## **Channel and Controller**



### Main Memory Implementation



10/02/2017 (© J.P. Shen)

18-600 Lecture #10

# 18-600 Foundations of Computer Systems

## Lecture 10: "The Memory Hierarchy"

- A. Memory Technologies
- B. Main Memory Implementation
  - a. DRAM Organization
  - b. DRAM Operation
  - c. Memory Controller
- C. Disk Storage Technologies



10/02/2017 (© John Shen)

### Page Mode DRAM

- A DRAM bank is a 2D array of cells: rows x columns
- A "DRAM row" is also called a "DRAM page"
- "Sense amplifiers" also called "row buffer"
- Each address is a <row,column> pair
- Access to a "closed row"
  - Activate command opens row (placed into row buffer)
  - Read/write command reads/writes column in the row buffer
  - Precharge command closes the row and prepares the bank for next access
- Access to an "open row"
  - No need for activate command

### DRAM (Bank) Operation



18-600 Lecture #10

# Original (Old) DRAM Read Timing



10/02/2017 (© J.P. Shen)

18-600 Lecture #10



10/02/2017 (© J.P. Shen)

18-600 Lecture #10



10/02/2017 (© J.P. Shen)

18-600 Lecture #10





10/02/2017 (© John Shen)

18-600 Lecture #10

### Enhanced DRAMs

- Basic DRAM cell has not changed since its invention in 1966.
  - Commercialized by Intel in 1970.
- DRAM cores with better interface logic and faster I/O :
  - Synchronous DRAM (SDRAM)
    - Uses a conventional clock signal instead of asynchronous control
    - Allows reuse of the row addresses (e.g., RAS, CAS, CAS, CAS)
  - Double data-rate synchronous DRAM (DDR SDRAM)
    - Double edge clocking sends two bits per cycle per pin
    - Different types distinguished by size of small prefetch buffer:
      - DDR (2 bits), DDR2 (4 bits), DDR3 (8 bits)
    - By 2010, standard for most server and desktop systems
    - Intel Core i7 supports only DDR3 SDRAM

Physical memory space



10/02/2017 (© J.P. Shen)

18-600 Lecture #10

Physical memory space



10/02/2017 (© J.P. Shen)

18-600 Lecture #10

Physical memory space



10/02/2017 (© J.P. Shen)

18-600 Lecture #10

Physical memory space



10/02/2017 (© J.P. Shen)

18-600 Lecture #10

Physical memory space



10/02/2017 (© J.P. Shen)

18-600 Lecture #10

Physical memory space



10/02/2017 (© J.P. Shen)

18-600 Lecture #10

Physical memory space



10/02/2017 (© J.P. Shen)

18-600 Lecture #10

# 18-600 Foundations of Computer Systems

## Lecture 10: "The Memory Hierarchy"

- A. Memory Technologies
- B. Main Memory Implementation
  - a. DRAM Organization
  - b. DRAM Operation
  - c. Memory Controller
- C. Disk Storage Technologies



10/02/2017 (© John Shen)

### Memory Controller



10/02/2017 (© J.P. Shen)

18-600 Lecture #10



18-600 Lecture #10

### Latency Components: Basic DRAM Operation

- CPU  $\rightarrow$  controller transfer time
- Controller latency
  - Queuing & scheduling delay at the controller
  - Access converted to basic commands
- Controller  $\rightarrow$  DRAM transfer time
- DRAM bank latency
  - Simple CAS if row is "open" OR
  - RAS + CAS if array precharged OR
  - PRE + RAS + CAS (worst case)
- DRAM → CPU transfer time (through controller)



- A: Transaction request may be delayed in Queue B: Transaction request sent to Memory Controller C: Transaction converted to Command Sequences (may be queued)
- D: Command/s Sent to DRAM
- E<sub>1</sub>: Requires only a CAS or
- E<sub>2</sub>: Requires **RAS + CAS** or
- E3: Requires PRE + RAS + CAS
- F: Transaction sent back to CPU

"DRAM Latency" = A + B + C + D + E + F

# 18-600 Foundations of Computer Systems

## Lecture 10: "The Memory Hierarchy"

- A. Memory Technologies
- B. Main Memory Implementation
  - a. DRAM Organization
  - b. DRAM Operation
  - c. Memory Controller
- C. Disk Storage Technologies



Carnegie Mellon University 66

10/02/2017 (© John Shen)

# Typical Computer Organization



18-600 Lecture #10

### What's Inside A Disk Drive?



# Disk Geometry

- Disks consist of platters, each with two surfaces.
- Each surface consists of concentric rings called tracks.
- Each track consists of sectors separated by gaps.
- Aligned tracks form a cylinder.



# Disk Capacity

Capacity = (# bytes/sector) x (avg. # sectors/track) x (# tracks/surface) x (# surfaces/platter) x (# platters/disk)

Example:

- 512 bytes/sector
- 300 sectors/track (on average)
- 20,000 tracks/surface
- 2 surfaces/platter
- 5 platters/disk

```
Capacity = 512 x 300 x 20000 x 2 x 5
```

- = 30,720,000,000
  - = 30.72 GB

## Disk Operation



The read/write *head* is attached to the end of the *arm* and flies over the disk surface on a thin cushion of air.

> By moving radially, the arm can position the read/write head over any track.



#### Multi-Platter View

Single-Platter View

spindle

10/02/2017 (© John Shen)

18-600 Lecture #10

### Disk Access

### Head in position above a track

### Rotation is counter-clockwise
### Disk Access – Read



About to read blue sector

After BLUE read

### Disk Access of RED



### Disk Access Time

- Average time to access some target sector approximated by :
  - Taccess = Tavg seek + Tavg rotation + Tavg transfer
- Seek time (Tavg seek)
  - Time to position heads over cylinder containing target sector.
  - Typical Tavg seek is 3–9 ms
- Rotational latency (Tavg rotation)
  - Time waiting for first bit of target sector to pass under r/w head.
  - Tavg rotation = 1/2 x 1/RPMs x 60 sec/1 min
  - Typical Tavg rotation = 7200 RPMs
- Transfer time (Tavg transfer)
  - Time to read the bits in the target sector.
  - Tavg transfer = 1/RPM x 1/(avg # sectors/track) x 60 secs/1 min.

# Disk Access Time Example

- Given:
  - Rotational rate = 7,200 RPM
  - Average seek time = 9 ms.
  - Avg # sectors/track = 400.
- Derived:
  - Tavg rotation = 1/2 x (60 secs/7200 RPM) x 1000 ms/sec = 4 ms.
  - Tavg transfer = 60/7200 RPM x 1/400 secs/track x 1000 ms/sec = 0.02 ms
  - Taccess = 9 ms + 4 ms + 0.02 ms
- Important points:
  - Access time dominated by seek time and rotational latency.
  - First bit in a sector is the most expensive, the rest are free.
  - SRAM access time is about 4 ns/doubleword, DRAM about 60 ns
    - Disk is about 40,000 times slower than SRAM,
    - 2,500 times slower then DRAM.

## Logical Disk Blocks

- Modern disks present a simpler abstract view of the complex sector geometry:
  - The set of available sectors is modeled as a sequence of b-sized logical blocks (0, 1, 2, ...)
- Mapping between logical blocks and actual (physical) sectors
  - Maintained by hardware/firmware device called disk controller.
  - Converts requests for logical blocks into (surface,track,sector) triples.
- Allows controller to set aside spare cylinders for each zone.
  - Accounts for the difference in "formatted capacity" and "maximum capacity".



10/02/2017 (© John Shen)

18-600 Lecture #10

Carnegie Mellon University 78

## Reading a Disk Sector (1)



10/02/2017 (© John Shen)

18-600 Lecture #10

# Reading a Disk Sector (2)



10/02/2017 (© John Shen)

18-600 Lecture #10

Carnegie Mellon University 80

## Reading a Disk Sector (3)



10/02/2017 (© John Shen)

18-600 Lecture #10

#### Carnegie Mellon University<sup>81</sup>

## Nonvolatile Memories

- DRAM and SRAM are volatile memories
  - Lose information if powered off.
- Nonvolatile memories retain value even if powered off
  - Read-only memory (ROM): programmed during production
  - Programmable ROM (PROM): can be programmed once
  - Erasable PROM (EPROM): can be bulk erased (UV, X-Ray)
  - Electrically erasable PROM (EEPROM): electronic erase capability
  - Flash memory: EEPROMs. with partial (block-level) erase capability
    - Wears out after about 100,000 erasing cycles
- Uses for Nonvolatile Memories
  - Firmware programs stored in a ROM (BIOS, controllers for disks, network cards, graphics accelerators, security subsystems,...)
  - Solid state disks (replace rotating disks in thumb drives, smart phones, mp3 players, tablets, laptops,...)
  - Disk caches



EPROM device structure



- Pages: 512B to 4KB, Blocks: 32 to 128 pages
- Data read/written in units of pages.
- Page can be written only after its block has been erased
- A block wears out after about 100,000 repeated writes.

# SSD Tradeoffs vs Rotating Disks

- Advantages
  - No moving parts  $\rightarrow$  faster, less power, more rugged
- Disadvantages
  - Have the potential to wear out
    - Mitigated by "wear leveling logic" in flash translation layer
    - E.g. Intel SSD 730 guarantees 128 petabyte (128 x 10<sup>15</sup> bytes) of writes before they wear out
  - In 2015, about 30 times more expensive per byte
- Applications
  - MP3 players, smart phones, laptops
  - Beginning to appear in desktops and servers (as disk cache)

## The CPU-Memory-Storage Gaps



10/02/2017 (© John Shen)

18-600 Lecture #10

#### Carnegie Mellon University<sup>85</sup>

# 18-600 Foundations of Computer Systems

### Lecture 11: "Cache Memories & Multicore Processors"

John P. Shen & Gregory Kesden October 4, 2017

Next Time

Required Reading Assignment:

• Chapter 6 of CS:APP (3<sup>rd</sup> edition) by Randy Bryant & Dave O'Hallaron.



10/02/2017 (© John Shen)

18-600 Lecture #10

Carnegie Mellon University<sup>86</sup>